

# **N-Channel Depletion-Mode DMOS FET**

#### **Features**

- Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- **Excellent thermal stability**
- Integral source-drain diode
- High input impedance and low C<sub>ISS</sub>
- ESD gate protection

#### **Applications**

- Solid state relays
- Normally-on switches
- Converters
- Power supply circuits
- Constant current sources
- Input protection circuits

#### **General Description**

The LND250 is a high voltage N-channel depletion mode (normally-on) transistor utilizing Supertex's lateral DMOS technology. The gate is ESD protected.

The LND250 is ideal for high voltage applications in the areas of normally-on switches, precision constant current sources, voltage ramp generation and amplification.

## **Ordering Information**

Part Number	Package Options	Packing		
LND250K1-G*	TO-236AB (SOT-23)	3000/Reel		

<sup>-</sup>G denotes a lead (Pb)-free / RoHS compliant package

## **Absolute Maximum Ratings**

Parameter	Value
Drain-to-source	BV <sub>DSX</sub>
Drain-to-gate	BV <sub>DGX</sub>
Gate-to-source	±20V
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

#### **Product Summary**

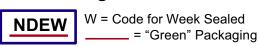
BV <sub>DSX</sub> /BV <sub>DGX</sub>	R <sub>DS(ON)</sub>	DSS
(V)	(max)	(min)
500	1.0kΩ	1.0mA

## **Pin Configuration**



TO-236AB (SOT-23)

## **Product Marking**



TO-236AB (SOT-23)

Packages may or may not include the following marks: Si or



Part is not recommended for new designs. Please refer to LND150K1-G.

## **Thermal Characteristics**

Package	$ \begin{vmatrix} \mathbf{I}_{\mathrm{D}} & \mathbf{I}_{\mathrm{D}} \\ (\mathrm{continuous})^{\dagger} & (\mathrm{pulsed}) \\ (\mathrm{mA}) & (\mathrm{mA}) \end{vmatrix} $		Power Dissipation @T <sub>A</sub> = 25°C (W)	θ <sub>ja</sub> (°C/W)	l <sub>DR</sub> (mA)	l <sub>DRM</sub> <sup>†</sup> (mA)	
TO-236AB (SOT-23)	13	30	0.36	203	13	30	

#### Notes:

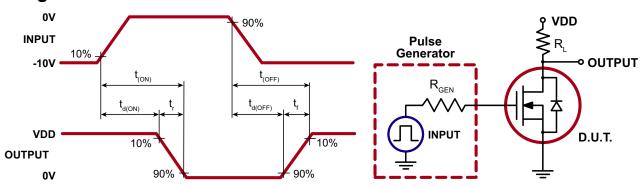
# **Electrical Characteristics** (T<sub>A</sub> = 25°C unless otherwise specified)

Sym	Parameter	Min	Тур	Max	Units	Conditions	
BV <sub>DSX</sub>	Drain-to-source breakdown voltage	500	-	-	V	$V_{GS} = -10V, I_{D} = 1.0 \text{mA}$	
$V_{\rm GS(OFF)}$	Gate-to-source off voltage	-1.0	-	-3.0	V	V <sub>GS</sub> = 25V, I <sub>D</sub> = 100nA	
$\Delta V_{\text{GS(OFF)}}$	Change in V <sub>GS(OFF)</sub> with temperature	-	-	5.0	mV/°C	$V_{GS} = 25V, I_{D} = 100nA$	
I <sub>GSS</sub>	Gate body leakage current	_	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
		-	-	100	nA	$V_{GS} = -10V, V_{DS} = 450V$	
I <sub>D(OFF)</sub>	Drain-to-source leakage current	-	-	100	μA	$V_{DS} = 0.8V$ Max Rating, $V_{GS} = -10V$ , $T_A = 125^{\circ}C$	
I <sub>DSS</sub>	Saturated drain-to-source current	1.0	-	3.0	mA	$V_{GS} = 0V, V_{DS} = 25V$	
R <sub>DS(ON)</sub>	Static drain-to-source on-state resistance	-	850	1000	Ω	$V_{GS} = 0V, I_D = 0.5mA$	
$\Delta R_{DS(ON)}$	Change in R <sub>DS(ON)</sub> with temperature	-	-	1.2	%/°C	$V_{GS} = 0V, I_D = 0.5mA$	
G <sub>FS</sub>	Forward transductance	1.0	2.0	-	mmho	$V_{DS} = 0V, I_{D} = 1.0 \text{mA}$	
C <sub>ISS</sub>	Input capacitance	-	7.5	10		V <sub>GS</sub> = -10V,	
C <sub>oss</sub>	Common source output capacitance	-	2.0	3.5	pF	$V_{DS} = 25V$	
C <sub>RSS</sub>	Reverse transfer capacitance	-	0.5	1.0		f = 1.0MHz	
t <sub>d(ON)</sub>	Turn-on delay time	-	0.09	-		V <sub>DD</sub> = 25V,	
t <sub>r</sub>	Rise time	-	0.45	-			
t <sub>d(OFF)</sub>	Turn-off delay time	-	0.1	-	μs	$\begin{vmatrix} I_D = 1.0 \text{mA}, \\ R_{GEN} = 25 \Omega \end{vmatrix}$	
t <sub>f</sub>	Fall time	-	1.3	-		GLIN	
V <sub>SD</sub>	Diode forward voltage drop	-	-	0.9	V	V <sub>GS</sub> = -10V, I <sub>SD</sub> = 1.0mA	
t <sub>rr</sub>	Reverse recovery time	-	200	-	ns	V <sub>GS</sub> = -10V, I <sub>SD</sub> = 1.0mA	

#### Notes:

- 1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
- 2. All A.C. parameters sample tested.

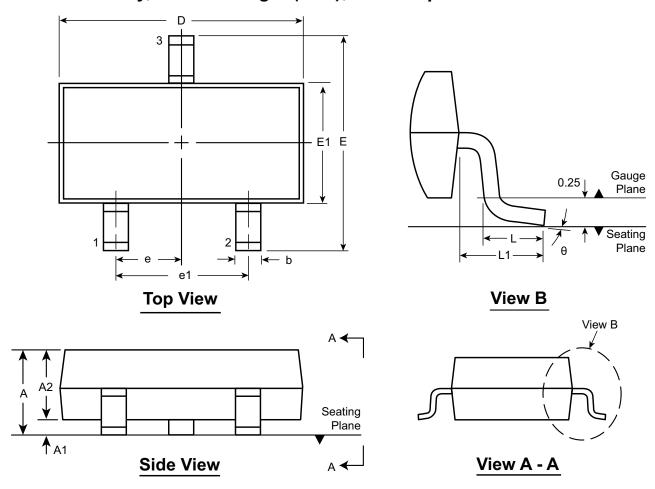
# **Switching Waveforms and Test Circuit**



 $<sup>\</sup>dagger$  I<sub>D</sub> (continuous) is limited by max rated T<sub>r</sub>

# 3-Lead TO-236AB (SOT-23) Package Outline (K1)

2.90x1.30mm body, 1.12mm height (max), 1.90mm pitch



Symb	ol	Α	A1	A2	b	D	E	E1	е	e1	L	L1	θ	
Dimension (mm)	MIN	0.89	0.01	0.88	0.30	2.80	2.10	1.20	0.05	1.90 BSC		0.20†	0.54	<b>0</b> °
	NOM	-	-	0.95	-	2.90	-	1.30	0.95 BSC		0.50	0.54 REF	-	
	MAX	1.12	0.10	1.02	0.50	3.04	2.64	1.40	000	ВОС	0.60	IXLI	<b>8</b> º	

JEDEC Registration TO-236, Variation AB, Issue H, Jan. 1999.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO236ABK1, Version C041309.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <a href="http://www.supertex.com/packaging.html">http://www.supertex.com/packaging.html</a>.)

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<sup>†</sup> This dimension differs from the JEDEC drawing.

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